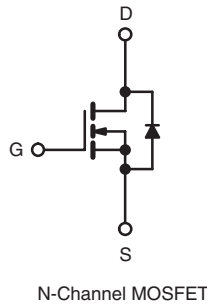


## Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	500
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$   0.27
$Q_g$ (Max.) (nC)	210
$Q_{gs}$ (nC)	29
$Q_{gd}$ (nC)	110
Configuration	Single

**TO-247**


### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available


 Available  
**RoHS\***  
 COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP460PbF
	SiHFP460-E3
SnPb	IRFP460
	SiHFP460

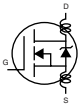

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	500	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A	
		$T_C = 100\text{ }^\circ\text{C}$		
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	80		
Linear Derating Factor		2.2	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	960	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$	20	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	28	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	280	W
Peak Diode Recovery $dV/dt^c$		$dV/dt$	3.5	V/ns
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 4.3\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 20\text{ A}$  (see fig. 12).
- $I_{SD} \leq 20\text{ A}$ ,  $dI/dt \leq 160\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.24	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.45	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.63	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 12\text{ A}^b$	-	-	0.27	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 12\text{ A}^b$		13	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$ , see fig. 5		-	4200	-	pF
Output Capacitance	$C_{oss}$			-	870	-	
Reverse Transfer Capacitance	$C_{riss}$			-	350	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 <sup>b</sup>	-	-	210	nC
Gate-Source Charge	$Q_{gs}$			-	-	29	
Gate-Drain Charge	$Q_{gd}$			-	-	110	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 20\text{ A},$ $R_G = 4.3\text{ }\Omega, R_D = 13\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	18	-	ns
Rise Time	$t_r$			-	59	-	
Turn-Off Delay Time	$t_{d(off)}$			-	110	-	
Fall Time	$t_f$			-	58	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	5.0	-	nH
Internal Source Inductance	$L_S$			-	13	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	20	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	80	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 20\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.8	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 20\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	570	860	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	5.7	8.6	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$



Fig. 3 - Typical Transfer Characteristics



Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

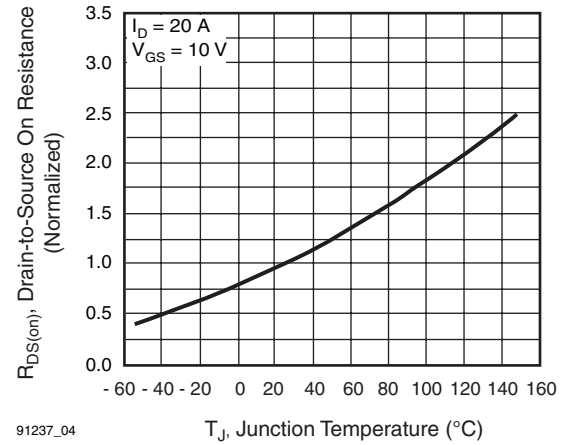
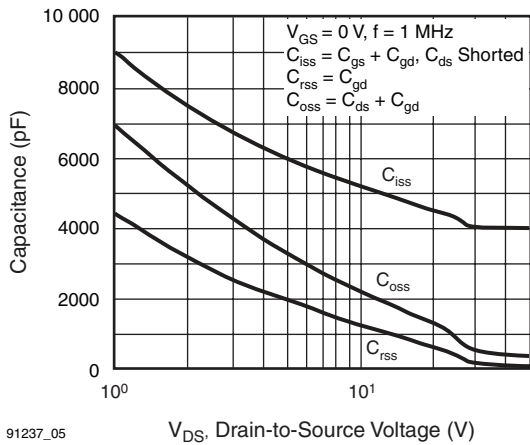
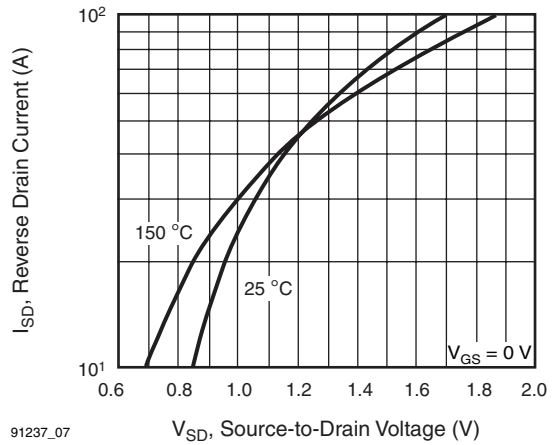


Fig. 4 - Normalized On-Resistance vs. Temperature



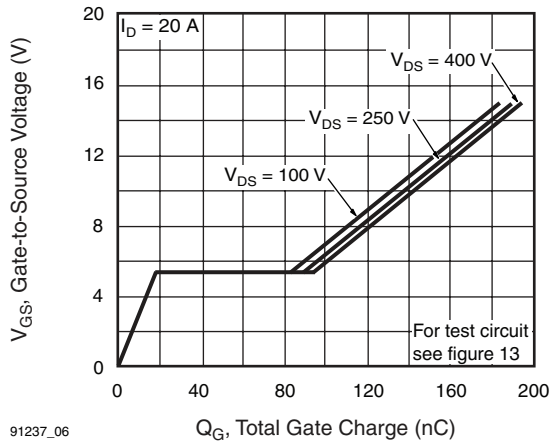
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



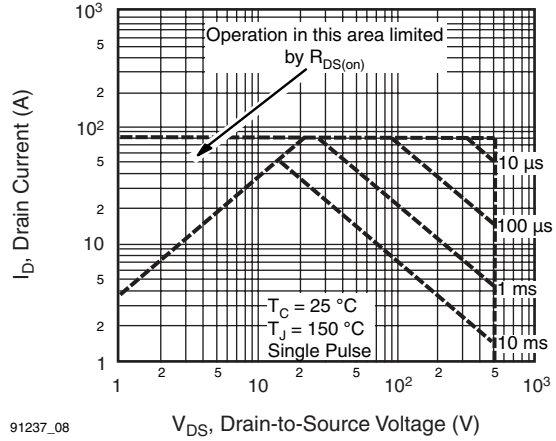
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91237\_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91237\_08

Fig. 8 - Maximum Safe Operating Area



91237\_09

**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 10a - Switching Time Test Circuit**



**Fig. 10b - Switching Time Waveforms**



91237\_11

**Fig. 11a - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



**Fig. 12a - Unclamped Inductive Test Circuit**



**Fig. 12b - Unclamped Inductive Waveforms**



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

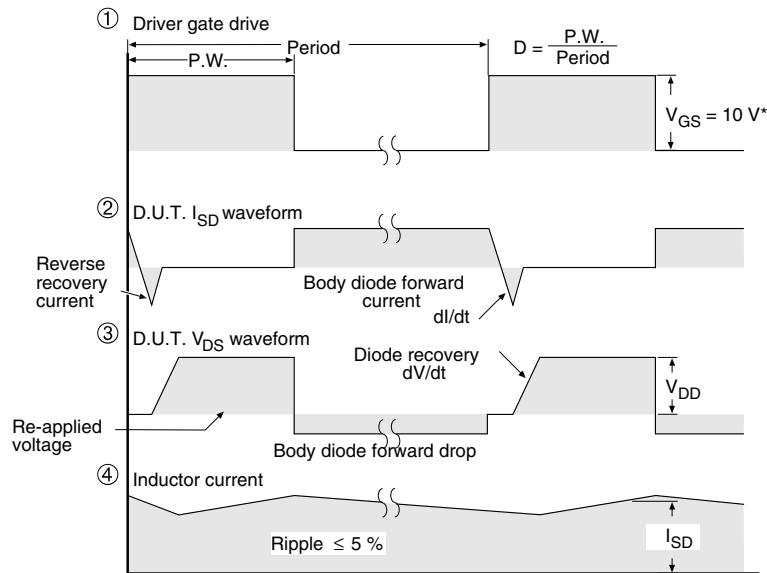


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

## Peak Diode Recovery $dV/dt$ Test Circuit



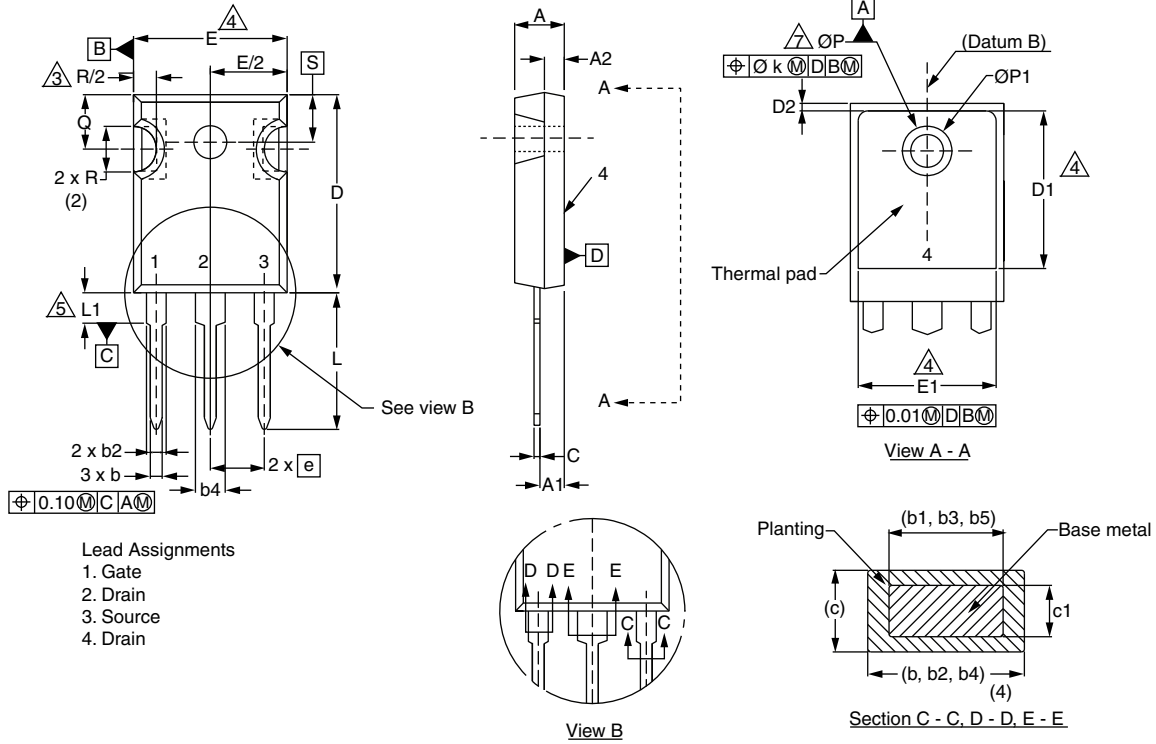
\*  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-247AC (High Voltage)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: X13-0103-Rev. D, 01-Jul-13  
 DWG: 5971

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.







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